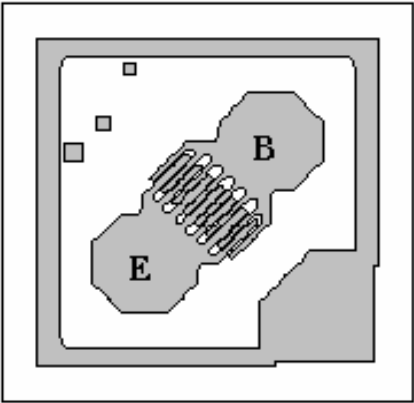




2SC2732 NPN EPITAXIAL SILICON TRANSISTORS

NPN EPITAXIAL SILICON TRANSISTORS			2SC2732			
High Frequency Transistor						
* Die Size 400*400 mkm * Metallization Top Al Typ. 0.9 mkm Back Au Typ.1.2 mkm * Die Thickness Typ. 220 mkm * Passivation Silicon Dioxide * Bonding Pad Size Emitter 90*90 mkm Base 90*90 mkm						
						
GUARANTEED PROBED CHARACTERISTICS (Ta=25° C)						
Characteristics	Symbol	Test Conditions	Limits			Units
			Min	Typ	Max	
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA, I_B=0$	25	-	-	V
Collector-Base Breakdown Voltage	V_{CBO}	$I_C=10mA, I_E=0$	30	-	-	V
Emitter-Base Breakdown Voltage	V_{EBO}	$I_E=10mA, I_C=0$	4.0	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB}=10V, I_E=0$	-	-	0.5	mkA
DC Current Gain	h_{FE}	$V_{CE}=10V, I_C=3mA$	30	60	-	
Collector-Emitter Saturation Voltage	V_{CESat}	$I_C=10mA, I_B=1.0mA$	-	-	5.0	V
Collector Output Capacitance	Cob	$V_{CB}=10V, f=1.0MHz$	-	-	0.8	pF
Transition Frequency	f_T	$V_{CE}=10V, I_C=5mA, f=100MHz$	700	1000	-	MHz
Conversion Gain	CG	$V_{CE}=12V, I_C=1mA, f=900MHz$		7.0		dB
Noise Figure	F	$V_{CE}=12V, I_C=1mA, f=900MHz$		10		dB
NOTES: Due to probe testing limitations, only the DC parameters are tested.						



2SC2732 NPN EPITAXIAL SILICON TRANSISTORS

NPN EPITAXIAL SILICON TRANSISTORS 2SC2735

High Frequency Transistor

* Die Size 400*400 mkm

* Metallization

Top Al Typ. 0.9 mkm

Back Au Typ.1.2 mkm

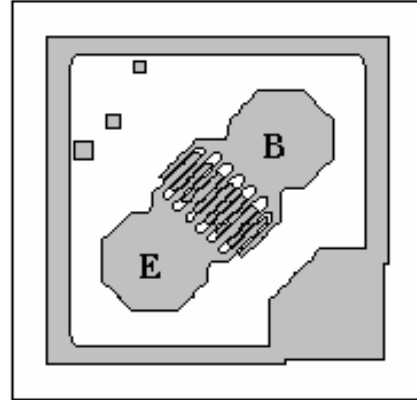
* Die Thickness Typ. 220 mkm

* Passivation Silicon Dioxide

* Bonding Pad Size

Emitter 90*90 mkm

Base 90*90 mkm



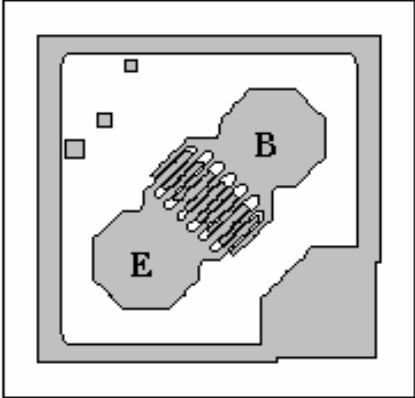
GUARANTEED PROBED CHARACTERISTICS (Ta=25° C)

Characteristics	Symbol	Test Conditions	Limits			Units
			Min	Typ	Max	
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA, I_B=0$	20	-	-	V
Collector-Base Breakdown Voltage	V_{CBO}	$I_C=10mA, I_E=0$	30	-	-	V
Emitter-Base Breakdown Voltage	V_{EBO}	$I_E=10mA, I_C=0$	3.0	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB}=10V, I_E=0$	-	-	0.5	mA
DC Current Gain	h_{FE}	$V_{CE}=10V, I_C=10mA$	40	-	-	
Collector-Emitter Saturation Voltage	V_{CESat}	$I_C=20mA, I_B=4.0mA$	-	-	1.0	V
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, f=1.0MHz$	-	-	1.5	pF
Transition Frequency	f_T	$V_{CE}=10V, I_C=10mA, f=100MHz$	600	1200	-	MHz
Conversion Gain	CG	$V_{CE}=12V, I_C=2mA, f=200MHz$	-	21	-	dB
Noise Figure	F	$V_{CE}=12V, I_C=2mA, f=200MHz$	-	6.5	-	dB

NOTES: Due to probe testing limitations, only the DC parameters are tested.



2SC2732 NPN EPITAXIAL SILICON TRANSISTORS

NPN EPITAXIAL SILICON TRANSISTORS			2SC2736			
High Frequency Transistor						
* Die Size 400*400 mkm * Metallization Top Al Typ. 0.9 mkm Back Au Typ.1.2 mkm * Die Thickness Typ. 220 mkm * Passivation Silicon Dioxide * Bonding Pad Size Emitter 90*90 mkm Base 90*90 mkm						
						
GUARANTEED PROBED CHARACTERISTICS (Ta=25°C)						
Characteristics	Symbol	Test Conditions	Limits			Units
			Min	Typ	Max	
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA, I_B=0$	20	-	-	V
Collector-Base Breakdown Voltage	V_{CBO}	$I_C=10mA, I_E=0$	30	-	-	V
Emitter-Base Breakdown Voltage	V_{EBO}	$I_E=10mA, I_C=0$	3.0	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB}=15V, I_E=0$	-	-	0.5	mA
DC Current Gain	h_{FE}	$V_{CE}=10V, I_C=5mA$	30	-	200	
Collector-Emitter Saturation Voltage	V_{CESat}	$I_C=10mA, I_B=5.0mA$	-	-	0.7	V
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, f=1.0MHz$	-	-	1.0	pF
Transition Frequency	f_T	$V_{CE}=10V, I_C=5mA, f=100MHz$	1400	2200	-	MHz
Conversion Gain	CG	$V_{CE}=12V, I_C=2mA, f=200MHz$	-	22.5	-	dB
Noise Figure	F	$V_{CE}=12V, I_C=2mA, f=200MHz$	-	4.0	-	dB
NOTES: Due to probe testing limitations, only the DC parameters are tested.						